VRW0;< ṂṂ Ł SQS ÆṀ ч s ǁ ˥ Silicon PNP transistor in a SOT-89 Plastic Package.

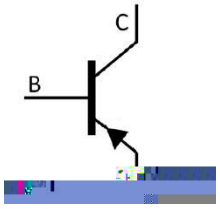
` ⅵ ɔ я ⅹ ı ѿ ⅻ ⅰ ớ Ḅ ı ت ⁼ я ᴗ Ḥ ı љ EU5VG4;<;T Й ´ ı ⅄ ᵀ DHF0T434 ‰´ ⅹ ˡ ˎ ớ ⌊ ∂ ı ṅ ⁽ ᵝ

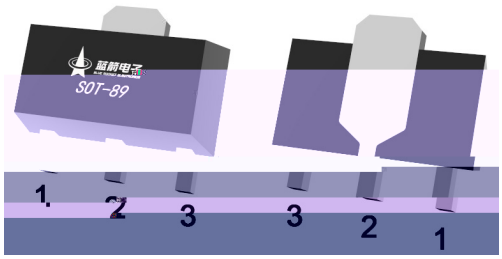
High breakdown voltage, good h_{FE} linearity, low $V_{CE(sat)}$, complements the BR2SD1898Q, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

˘ ı ˈ ѿ ⅻ ı ◗ ʼ ∩ ⊂ Ƶ ⅾ ⌧Є ⌊ ∂

General power amplifier applications, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit





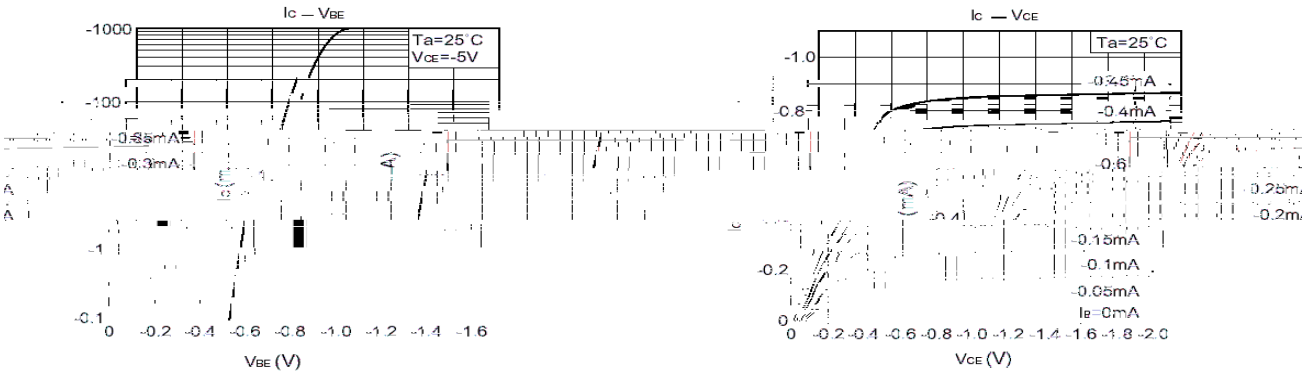
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

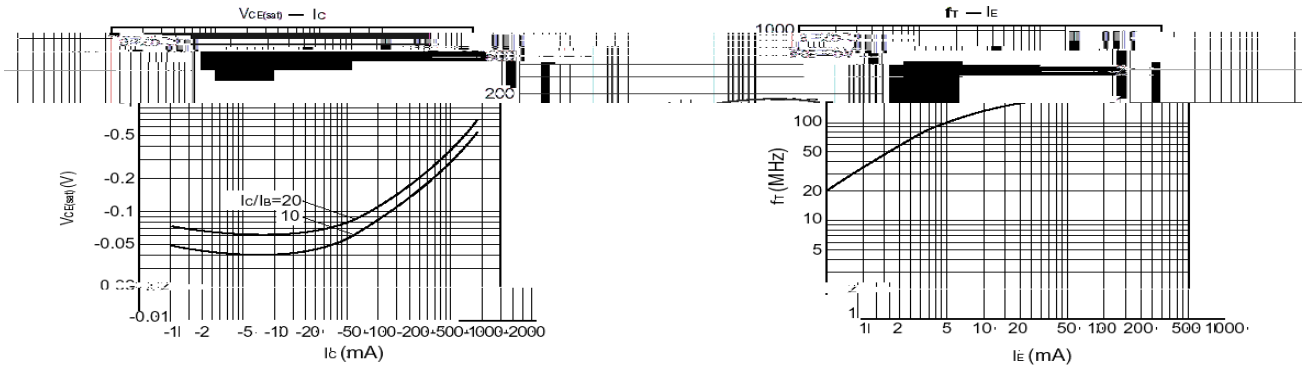
v ̈Ω Parameter	˧ N Symbol	̈Ω Ö Rating	D Ḫ Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-1.0	A
Collector Current-Continuous(Pulse)	*I_{CP}	-2.0	A
Collector Power Dissipation	**P_C	0.5	W
	*P_C	2.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

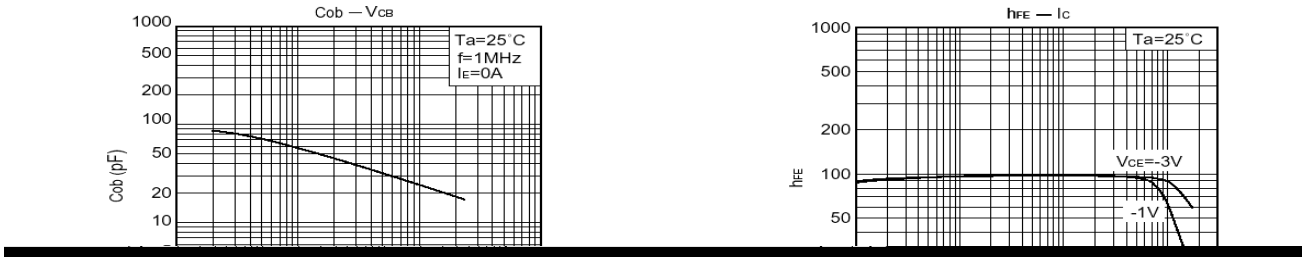
*Single pulse Pw=100ms ǐ˙ ⅃ ؛ ı ǐ Ḵ 100ms
**mounted on 40×40×0.7mm ceramic board Ɛ̂ ̂ 40×40×0.7m ⊞ ه i

v ̈Ω Parameter	˧ N Symbol	⅃ ؛ ǀ Ţ Test Conditions	ω ṇ Ö Min	Ɛ ʒ Ö Typ	ω ʑ Ö Max	D Ḫ Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-50μA I_E=0	-80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-1.0mA I_B=0	-80			V

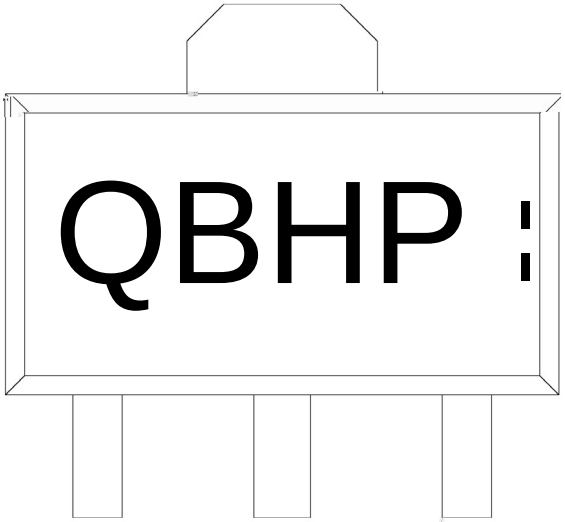
/ Electrical Characteristic Curve







/ Marking Instructions



ب ˝ χ	
T χ	ⱶ ∩ ⱹ ⱼ̀ ⱻ β ‰ ⱽ
BH χ	ⱶ ⱺ ᴺ ⱹ
P χ	ⱶ h_{FE} ʿ ⁶ ⱹ
-- χ	ⱶ ⱺ ⱻ ⱼ̈ ᴺ ⱹ ⱺ ⱻ ⱺ ⱻ ⱼ̈ ᴺ ⱹ Ȿ Ȿ

Note:

Q:	Automobile halogen-free product Code
BH:	Product Type
P χ	h_{FE} Classifications Symbol
**:	Lot No. Code, code change with Lot No

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)

ب ˝ χ

1 أ ♬ □ ỷ 150 Ḱ 200 ɬ ı `H ڑ 60 Ḱ 120sec;

2 Š Ö □ ỷ 255 ° 5 ɬ ı `H ڑ ˙Y ⁄ı ⁂ 5 ° 0.5sec;

3 ì ˙ ˥ ˛ ɔ ھ ỷ ⁂ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:150~200 ɬ , Time:60~120sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

/ Resistance to Soldering Heat Test Conditions

□ ỷ χ 260 ° 5 ɬ `H ڑ χ 10 ° 1 sec. Temp.:260±5 Time:10±1 sec